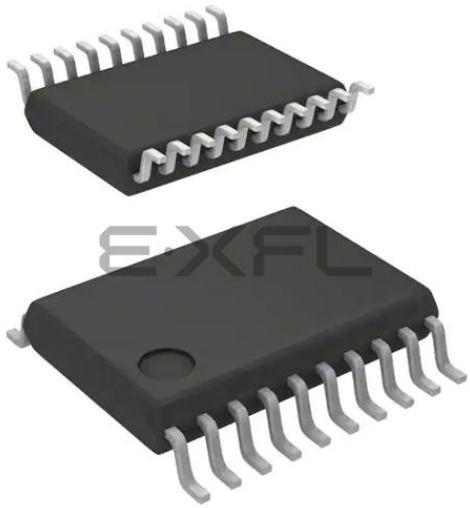

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	SIO, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	13
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	384 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21181dsp-u0

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1. Overview

These MCUs are fabricated using a high-performance silicon gate CMOS process, embedding the R8C/Tiny Series CPU core, and is packaged in a 20-pin molded-plastic LSSOP, SDIP or a 28-pin plastic molded-HWQFN. It implements sophisticated instructions for a high level of instruction efficiency. With 1 Mbyte of address space, they are capable of executing instructions at high speed.
Furthermore, the R8C/19 Group has on-chip data flash ROM (1 KB × 2 blocks).
The difference between the R8C/18 Group and R8C/19 Group is only the presence or absence of data flash ROM. Their peripheral functions are the same.

1.1 Applications

Electric household appliances, office equipment, housing equipment (sensors, security systems), general industrial equipment, audio equipment, etc.

Table 1.2 Functions and Specifications for R8C/19 Group

Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V)
	Operation mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to **Table 1.4 Product Information for R8C/19 Group**
Peripheral Functions	Ports	I/O ports: 13 pins (including LED drive port) Input port: 3 pins
	LED drive ports	I/O ports: 4 pins
	Timers	Timer X: 8 bits × 1 channel, timer Z: 8 bits × 1 channel (Each timer equipped with 8-bit prescaler) Timer C: 16 bits × 1 channel (Input capture and output compare circuits)
	Serial interfaces	1 channel Clock synchronous serial I/O, UART 1 channel UART
	Comparator	1-bit comparator: 1 circuit, 4 channels
	Watchdog timer	15 bits × 1 channel (with prescaler) Reset start selectable, count source protection mode
	Interrupts	Internal: 10 sources, External: 4 sources, Software: 4 sources, Priority levels: 7 levels
	Clock generation circuits	2 circuits • Main clock generation circuit (with on-chip feedback resistor) • On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has frequency adjustment function
	Oscillation stop detection function	Main clock oscillation stop detection function
	Voltage detection circuit	On-chip
	Power-on reset circuit	On-chip
Electric Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz)
	Current consumption	Typ. 9 mA (VCC = 5.0 V, f(XIN) = 20 MHz, comparator stopped) Typ. 5 mA (VCC = 3.0 V, f(XIN) = 10MHz, comparator stopped) Typ. 35 μA (VCC = 3.0 V, wait mode, peripheral clock off) Typ. 0.7 μA (VCC = 3.0 V, stop mode)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	10,000 times (data flash) 1,000 times (program ROM)
Operating Ambient Temperature		-20 to 85°C -40 to 85°C (D version)
Package		20-pin molded-plastic LSSOP
		20-pin molded-plastic SDIP
		28-pin molded-plastic HWQFN

1.3 Block Diagram

Figure 1.1 shows a Block Diagram.

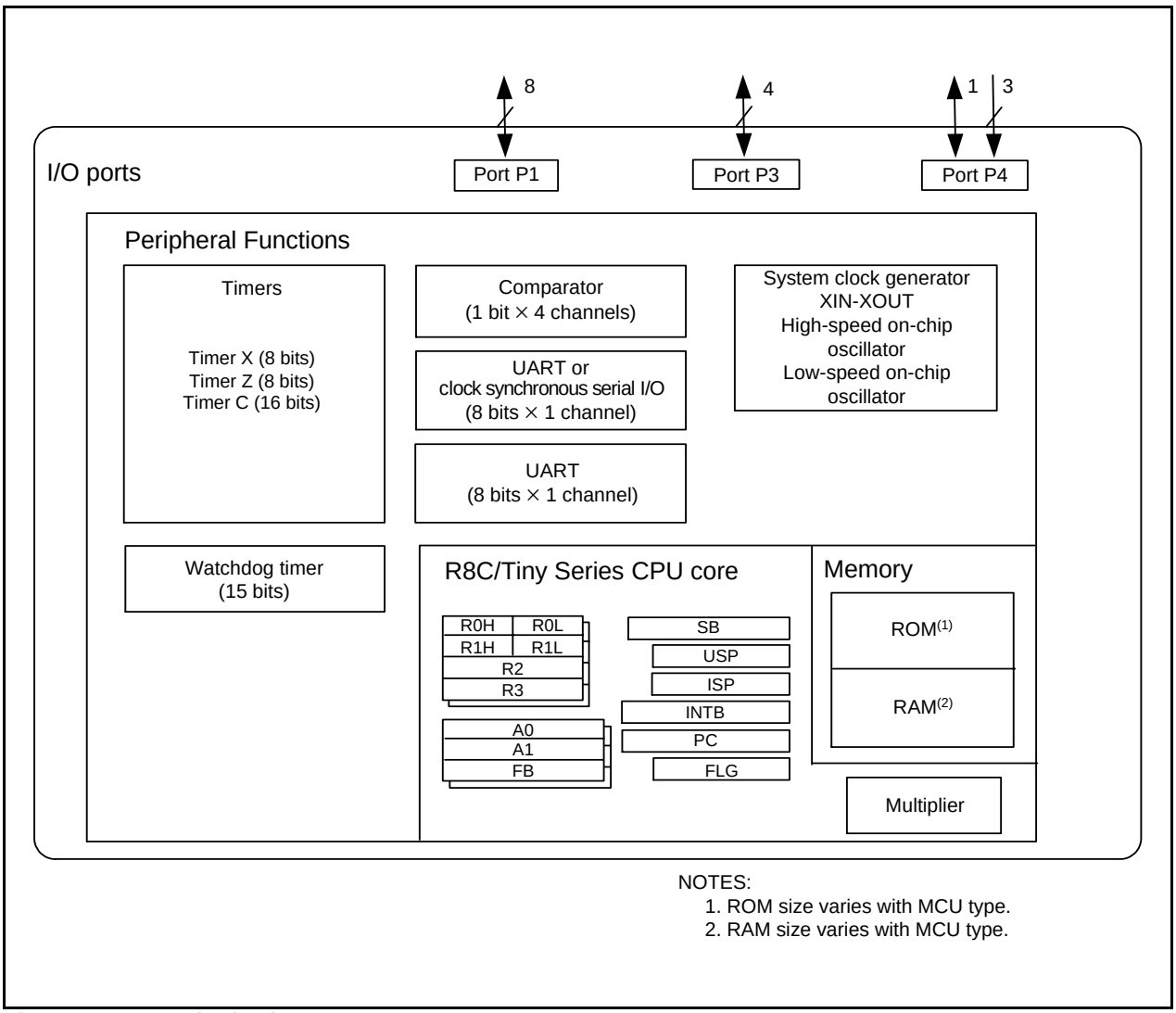


Figure 1.1 Block Diagram

1.4 Product Information

Table 1.3 lists Product Information for R8C/18 Group and Table 1.4 lists Product Information for R8C/19 Group.

Table 1.3 Product Information for R8C/18 Group **Current of Apr. 2006**

Type No.	ROM Capacity	RAM Capacity	Package Type	Remarks
R5F21181SP	4 Kbytes	384 bytes	PLSP0020JB-A	Flash memory version
R5F21182SP	8 Kbytes	512 bytes	PLSP0020JB-A	
R5F21183SP	12 Kbytes	768 bytes	PLSP0020JB-A	
R5F21184SP	16 Kbytes	1 Kbyte	PLSP0020JB-A	
R5F21181DSP (D)	4 Kbytes	384 bytes	PLSP0020JB-A	D version
R5F21182DSP (D)	8 Kbytes	512 bytes	PLSP0020JB-A	
R5F21183DSP (D)	12 Kbytes	768 bytes	PLSP0020JB-A	
R5F21184DSP (D)	16 Kbytes	1 Kbyte	PLSP0020JB-A	
R5F21181DD	4 Kbytes	384 bytes	PRDP0020BA-A	Flash memory version
R5F21182DD	8 Kbytes	512 bytes	PRDP0020BA-A	
R5F21183DD	12 Kbytes	768 bytes	PRDP0020BA-A	
R5F21184DD	16 Kbytes	1 Kbyte	PRDP0020BA-A	
R5F21182NP	8 Kbytes	512 bytes	PWQN0028KA-B	Flash memory version
R5F21183NP	12 Kbytes	768 bytes	PWQN0028KA-B	
R5F21184NP	16 Kbytes	1 Kbyte	PWQN0028KA-B	

(D): Under Development

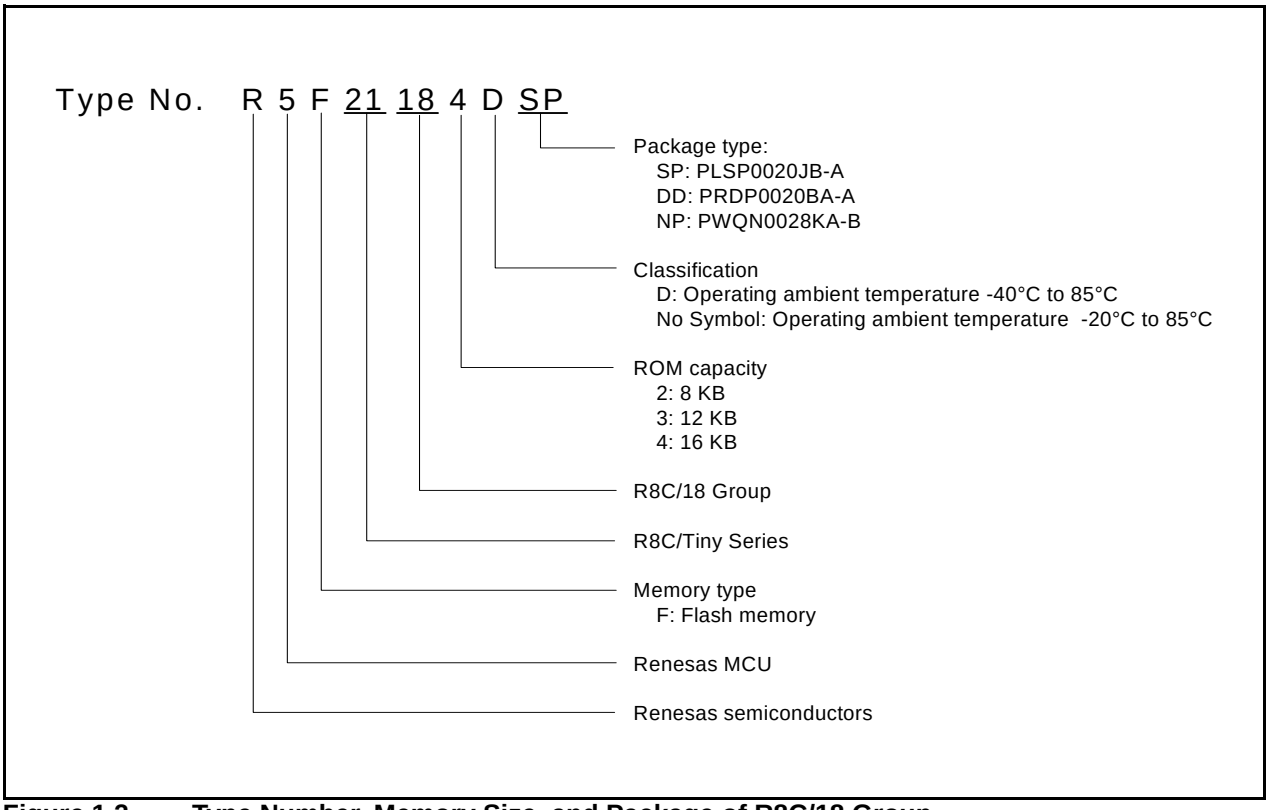


Figure 1.2 Type Number, Memory Size, and Package of R8C/18 Group

1.5 Pin Assignments

Figure 1.4 shows Pin Assignments for PLSP0020JB-A Package (Top View), Figure 1.5 shows Pin Assignments for PRDP0020BA-A Package (Top View) and Figure 1.6 shows Pin Assignments for PWQN0028KA-B Package (Top View).

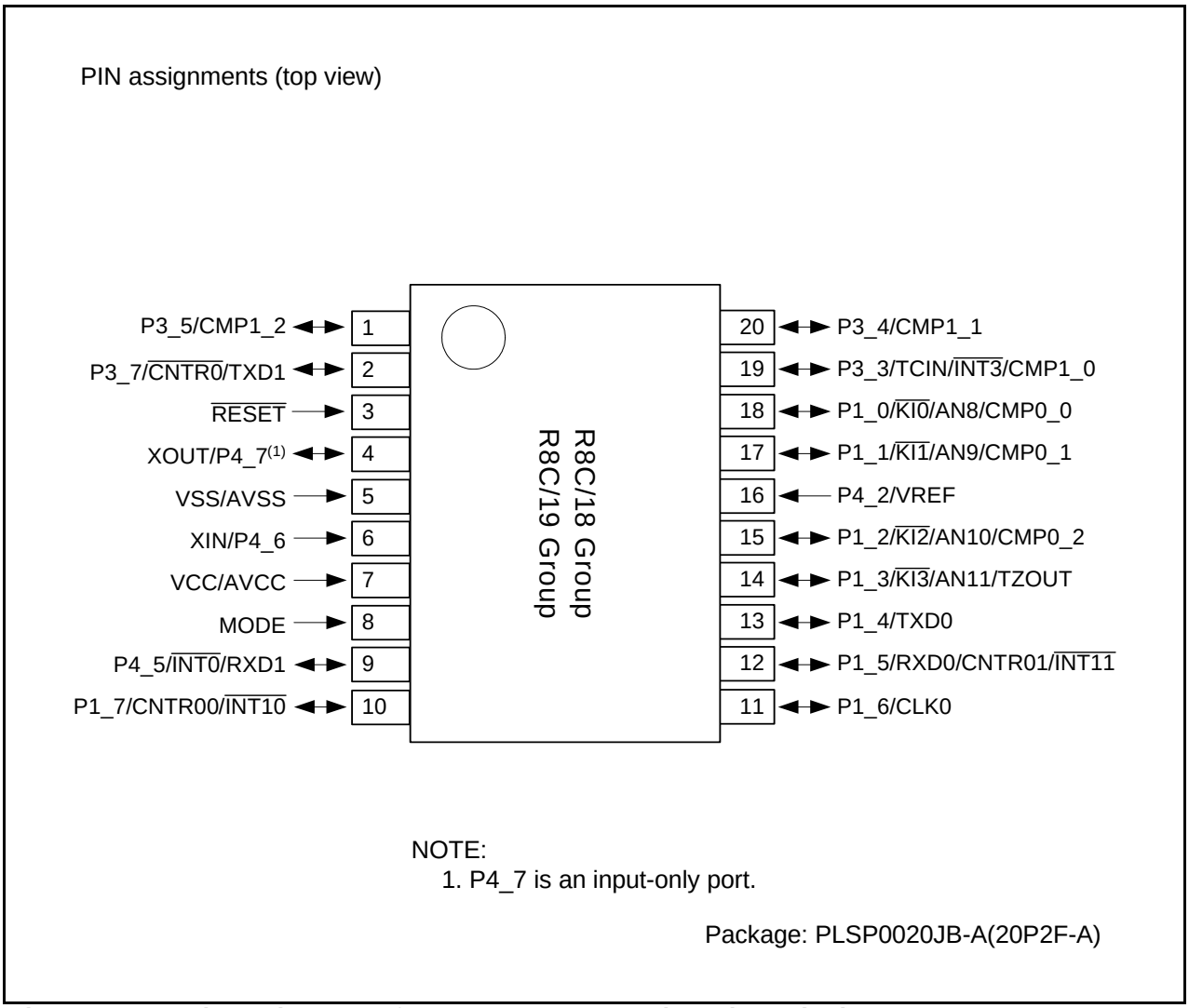


Figure 1.4 Pin Assignments for PLSP0020JB-A Package (Top View)

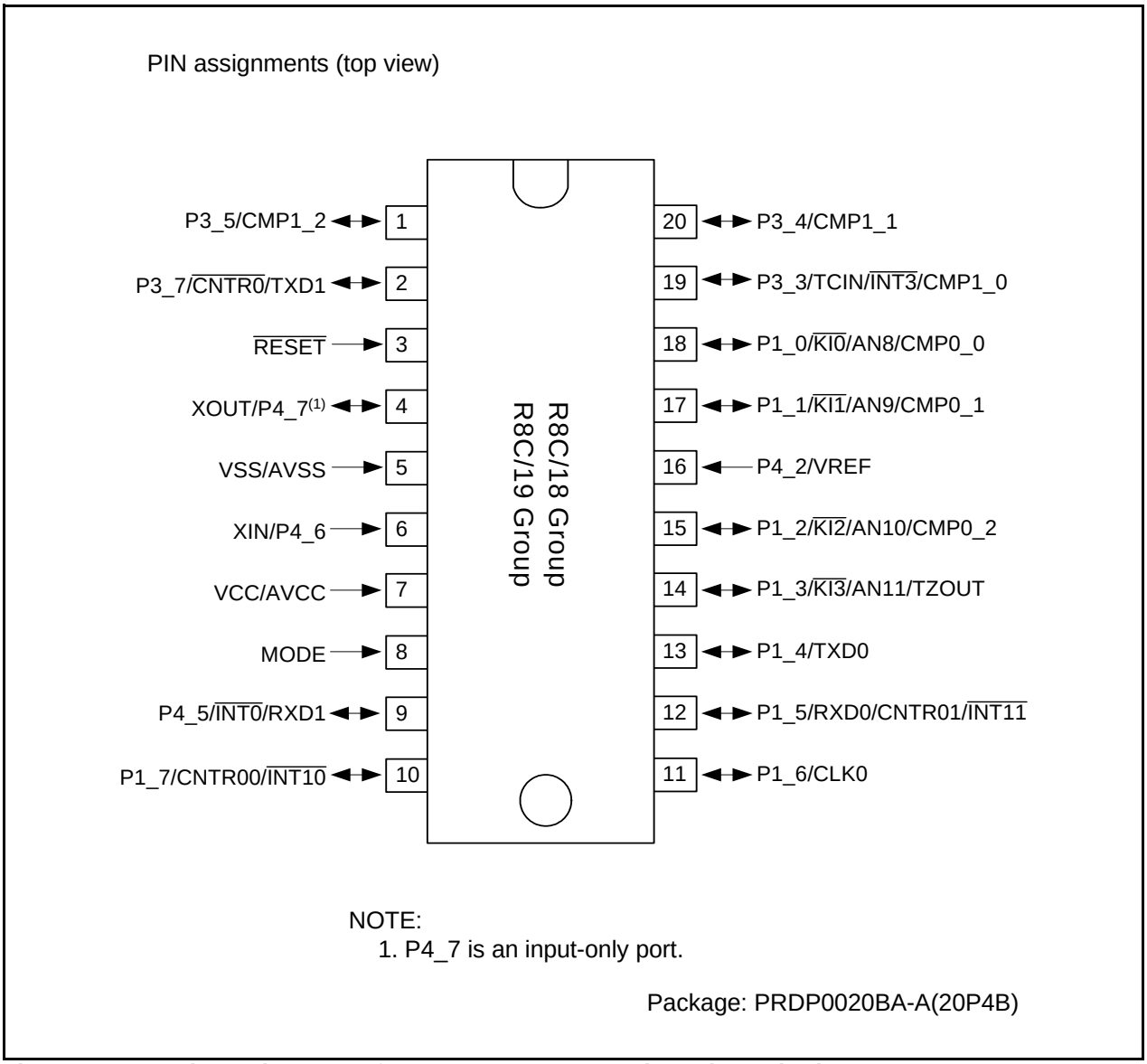


Figure 1.5 Pin Assignments for PRDP0020BA-A Package (Top View)

1.6 Pin Functions

Table 1.5 lists Pin Functions, Table 1.6 lists Pin Name Information by Pin Number of PLSP0020JB-A, PRDP0020BA-A packages, and Table 1.7 lists Pin Name Information by Pin Number of PWQN0028KA-B package.

Table 1.5 Pin Functions

Type	Symbol	I/O Type	Description
Power supply input	VCC VSS	I	Apply 2.7 V to 5.5 V to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	I	Power supply for the comparator Connect a capacitor between AVCC and AVSS.
Reset input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
Main clock input	XIN	I	These pins are provided for main clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins. To use an external clock, input it to the XIN pin and leave the XOUT pin open.
Main clock output	XOUT	O	
$\overline{\text{INT}}$ interrupt	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT3}}$	I	$\overline{\text{INT}}$ interrupt input pins
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer X	CNTR0	I/O	Timer X I/O pin
	$\overline{\text{CNTR0}}$	O	Timer X output pin
Timer Z	TZOUT	O	Timer Z output pin
Timer C	TCIN	I	Timer C input pin
	CMP0_0 to CMP0_2, CMP1_0 to CMP1_2	O	Timer C output pins
Serial interface	CLK0	I/O	Transfer clock I/O pin
	RXD0, RXD1	I	Serial data input pins
	TXD0, TXD1	O	Serial data output pins
Reference voltage input	VREF	I	Reference voltage input pin to comparator
Comparator	AN8 to AN11	I	Analog input pins to comparator
I/O port	P1_0 to P1_7, P3_3 to P3_5, P3_7, P4_5	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. P1_0 to P1_3 also function as LED drive ports.
Input port	P4_2, P4_6, P4_7	I	Input-only ports

I: Input O: Output I/O: Input and output

2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts.
Interrupts are disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.
The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is 3 bits wide, assigns processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has higher priority than IPL, the interrupt is enabled.

2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}	Supply voltage	V_{CC} = AV_{CC}	-0.3 to 6.5	V
AV_{CC}	Analog supply voltage	V_{CC} = AV_{CC}	-0.3 to 6.5	V
V_I	Input voltage		-0.3 to V_{CC}+0.3	V
V_O	Output voltage		-0.3 to V_{CC}+0.3	V
P_d	Power dissipation	T_{opr} = 25°C	300	mW
T_{opr}	Operating ambient temperature		-20 to 85 / -40 to 85 (D version)	°C
T_{stg}	Storage temperature		-65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}	Supply voltage			2.7	–	5.5	V
AV_{CC}	Analog supply voltage			–	V_{CC}	–	V
V_{SS}	Supply voltage			–	0	–	V
AV_{SS}	Analog supply voltage			–	0	–	V
V_{IH}	Input “H” voltage			0.8V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” voltage			0	–	0.2V_{CC}	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH\ (peak)}$		–	–	-60	mA
$I_{OH(peak)}$	Peak output “H” current			–	–	-10	mA
$I_{OH(avg)}$	Average output “H” current			–	–	-5	mA
$I_{OL(sum)}$	Peak sum output “L” currents	Sum of all pins $I_{OL\ (peak)}$		–	–	60	mA
$I_{OL(peak)}$	Peak output “L” currents	Except P1_0 to P1_3		–	–	10	mA
		P1_0 to P1_3	Drive capacity HIGH	–	–	30	mA
			Drive capacity LOW	–	–	10	mA
$I_{OL(avg)}$	Average output “L” current	Except P1_0 to P1_3		–	–	5	mA
		P1_0 to P1_3	Drive capacity HIGH	–	–	15	mA
			Drive capacity LOW	–	–	5	mA
$f_{(XIN)}$	Main clock input oscillation frequency		3.0 V ≤ V_{CC} ≤ 5.5 V	0	–	20	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, unless otherwise specified.
2. Typical values when average output current is 100 ms.

Table 5.3 Comparator Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Resolution		–	–	1	Bit
–	Absolute accuracy	ϕ_{AD} = 10 MHz(3)	–	–	±20	mV
t_{conv}	Conversion time	ϕ_{AD} = 10 MHz(3)	1	–	–	µs
V_{ref}	Reference voltage		0	–	AV_{CC}	V
V_{IA}	Analog input voltage		0	–	AV_{CC}	V
–	Comparator conversion operating clock frequency(2)		1	–	10	MHz

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, unless otherwise specified.
2. If f1 exceeds 10 MHz, divided f1 and ensure the comparator conversion operating clock frequency (ϕ_{AD}) is 10 MHz or below.
3. If AVcc is less than 4.2 V, divided f1 and ensure the comparator conversion operating clock frequency (ϕ_{AD}) is f1/2 or below.

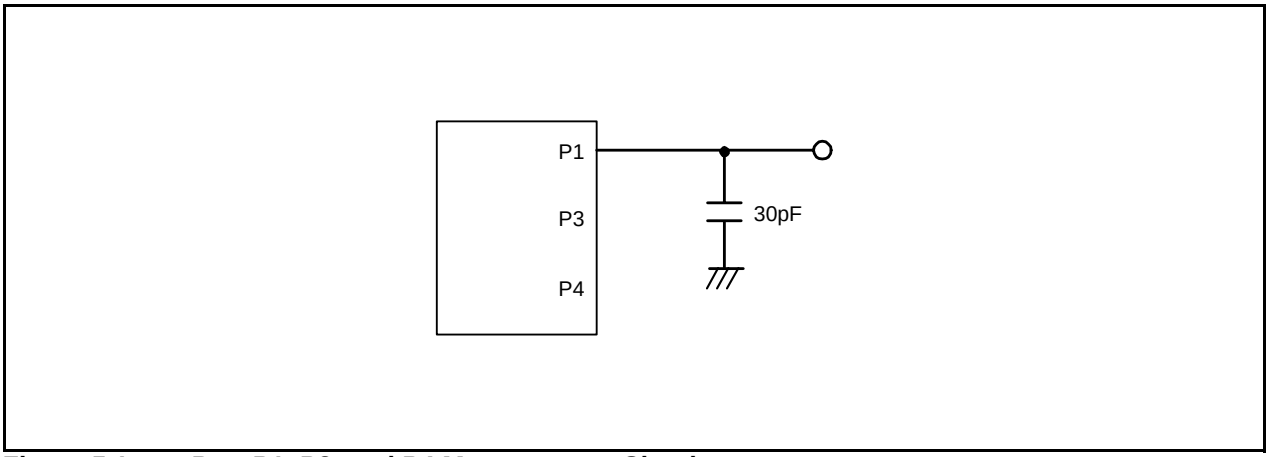


Figure 5.1 Port P1, P3, and P4 Measurement Circuit

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/18 Group	100(3)	–	–	times
		R8C/19 Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(8)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. If emergency processing is required, a suspend request can be generated independent of this characteristic. In that case the normal time delay to Suspend can be applied to the request.However, we recommend that a suspend request with an interval of less than 650 µs is only used once because, if the suspend state continues, erasure cannot operate and the incidence of erasure error rises.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the number of erase operations between block A and block B can further reduce the effective number of rewrites. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring programming/erasure failure rate information should contact their Renesas technical support representative.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (Program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (Program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (Program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (Program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		-20(8)	–	85	°C
–	Data hold time(9)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. If emergency processing is required, a suspend request can be generated independent of this characteristic. In that case the normal time delay to suspend can be applied to the request. However, we recommend that a suspend request with an interval of less than 650 µs is only used once because, if the suspend state continues, erasure cannot operate and the incidence of erasure error rises.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring programming/erasure failure rate information should contact their Renesas technical support representative.
8. -40 °C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

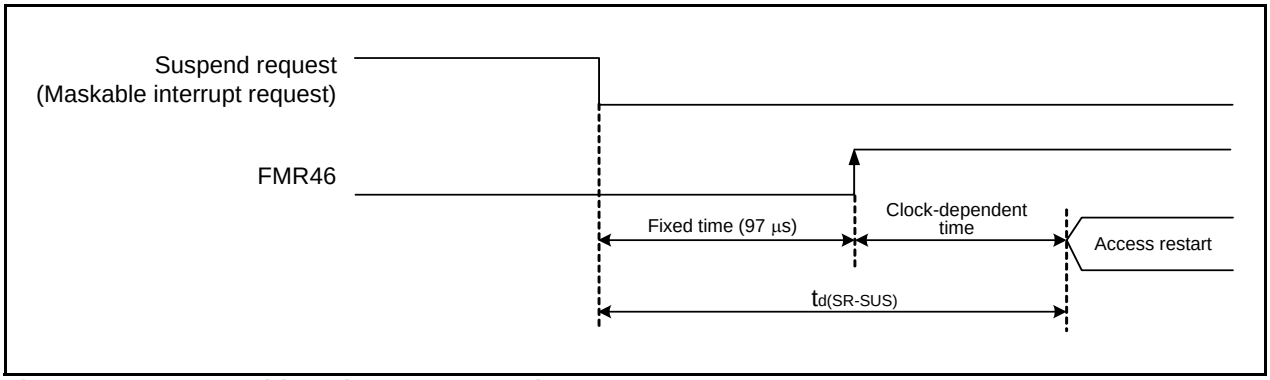


Figure 5.2 Transition Time to Suspend

Table 5.6 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(3)		2.70	2.85	3.00	V
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	600	–	nA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	100	µs
Vccmin	MCU operating voltage minimum value		2.7	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = -40°C to 85 °C.
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
3. Ensure that $V_{det2} > V_{det1}$.

Table 5.7 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level(4)		3.00	3.30	3.60	V
–	Voltage monitor 2 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	600	–	nA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = -40°C to 85 °C.
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.
4. Ensure that $V_{det2} > V_{det1}$.

Table 5.8 Reset Circuit Electrical Characteristics (When Using Voltage Monitor 1 Reset)

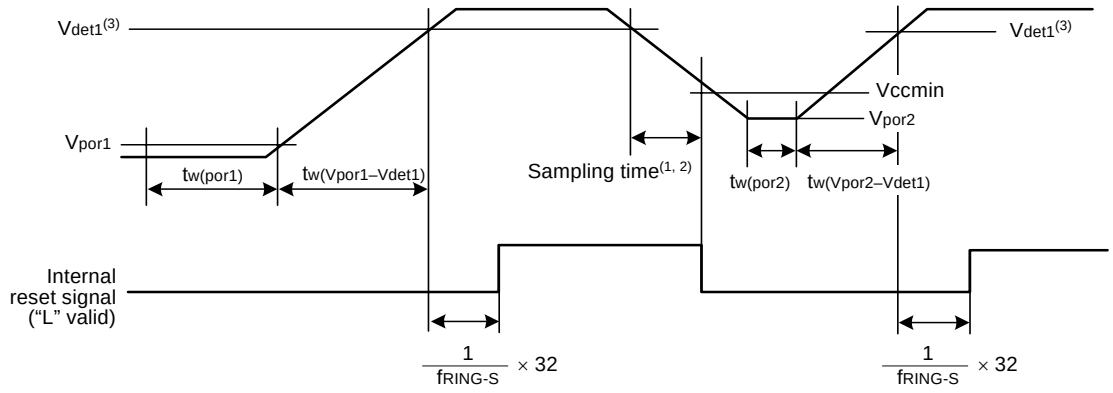
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por2}	Power-on reset valid voltage	-20°C ≤ Topr ≤ 85°C	–	–	V_{det1}	V
$t_{w(Vpor2-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted(1)	-20°C ≤ Topr ≤ 85°C, $t_{w(por2)}$ ≥ 0s(3)	–	–	100	ms

NOTES:
1. This condition is not applicable when using with Vcc ≥ 1.0 V.
2. When turning power on after the time to hold the external power below effective voltage (V_{por1}) exceeds10 s, refer to **Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset)**.
3. $t_{w(por2)}$ is the time to hold the external power below effective voltage (V_{por2}).

Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Power-on reset valid voltage	-20°C ≤ Topr ≤ 85°C	–	–	0.1	V
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	0°C ≤ Topr ≤ 85°C, $t_{w(por1)}$ ≥ 10 s(2)	–	–	100	ms
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	-20°C ≤ Topr < 0°C, $t_{w(por1)}$ ≥ 30 s(2)	–	–	100	ms
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	-20°C ≤ Topr < 0°C, $t_{w(por1)}$ ≥ 10 s(2)	–	–	1	ms
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	0°C ≤ Topr ≤ 85°C, $t_{w(por1)}$ ≥ 1 s(2)	–	–	0.5	ms

NOTES:
1. When not using voltage monitor 1, use with Vcc ≥ 2.7 V.
2. $t_{w(por1)}$ is the time to hold the external power below effective voltage (V_{por1}).



NOTES:
1. Hold the voltage inside the MCU operation voltage range (Vccmin or above) within the sampling time.
2. The sampling clock can be selected. Refer to **7. Voltage Detection Circuit** for details.
3. V_{det1} indicates the voltage detection level of the voltage detection 1 circuit. Refer to **7. Voltage Detection Circuit** for details.

Figure 5.3 Reset Circuit Electrical Characteristics

Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
–	High-speed on-chip oscillator frequency when the reset is deasserted	V_{CC} = 5.0 V, T_{opr} = 25 °C	–	8	–	MHz
–	High-speed on-chip oscillator frequency temperature supply voltage dependence(2)	0 to +60 °C/5 V ± 5 %(3)	7.76	–	8.24	MHz
		-20 to +85 °C/2.7 to 5.5 V(3)	7.68	–	8.32	MHz
		-40 to +85 °C/2.7 to 5.5 V(3)	7.44	–	8.32	MHz

NOTES:
1. The measurement condition is V_{CC} = 5.0 V and T_{opr} = 25 °C.
2. Refer to **10.6.4 High-Speed On-Chip Oscillator Clock** for notes on high-speed on-chip oscillator clock.
3. The standard value shows when the HRA1 register is assumed as the value in shipping and the HRA2 register value is set to 00h.

Table 5.11 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time(3)		–	–	150	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 to 5.5 V and T_{opr} = 25 °C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until CPU clock supply starts after the interrupt is acknowledged to exit stop mode.

Table 5.12 Electrical Characteristics (1) [Vcc = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
VOH	Output “H” voltage	Except XOUT	IOH = -5 mA		Vcc – 2.0	–	Vcc	V
			IOH = -200 µA		Vcc – 0.3	–	Vcc	V
		XOUT	Drive capacity HIGH	IOH = -1 mA	Vcc – 2.0	–	Vcc	V
			Drive capacity LOW	IOH = -500 µA	Vcc – 2.0	–	Vcc	V
VOL	Output “L” voltage	Except P1_0 to P1_3, XOUT	IOL = 5 mA		–	–	2.0	V
			IOL = 200 µA		–	–	0.45	V
		P1_0 to P1_3	Drive capacity HIGH	IOL = 15 mA	–	–	2.0	V
			Drive capacity LOW	IOL = 5 mA	–	–	2.0	V
			Drive capacity LOW	IOL = 200 µA	–	–	0.45	V
		XOUT	Drive capacity HIGH	IOL = 1 mA	–	–	2.0	V
			Drive capacity LOW	IOL = 500 µA	–	–	2.0	V
VT+-VT-	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, CNTR0, CNTR1, TCIN, RXD0			0.2	–	1.0	V
		$\overline{RESET}$			0.2	–	2.2	V
IIH	Input “H” current		VI = 5 V		–	–	5.0	µA
IIL	Input “L” current		VI = 0 V		–	–	-5.0	µA
RPULLUP	Pull-up resistance		VI = 0 V		30	50	167	kΩ
RfXIN	Feedback resistance	XIN			–	1.0	–	MΩ
fRING-S	Low-speed on-chip oscillator frequency				40	125	250	kHz
VRAM	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:
1. Vcc = 4.2 to 5.5 V at Topr = -20 to 85 °C / -40 to 85 °C, f(XIN) = 20 MHz, unless otherwise specified.

Table 5.20 Electrical Characteristics (4) [Vcc = 3V] (Topr = -40 to 85 °C, unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are Vss, comparator is stopped	High-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	8	13	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	7	12	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5	–	mA
		Medium-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.6	–	mA
		High-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	7.5	mA
			Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8 FMR47 = 1	–	100	280	µA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = 0	–	37	74	µA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = 0	–	35	70	µA
		Stop mode	Main clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = 0	–	0.7	3.0	µA

Table 5.24 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	300	–	ns
$t_{W(CKH)}$	CLKi input “H” width	150	–	ns
$t_{W(CKL)}$	CLKi input “L” width	150	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	80	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	70	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 or 1

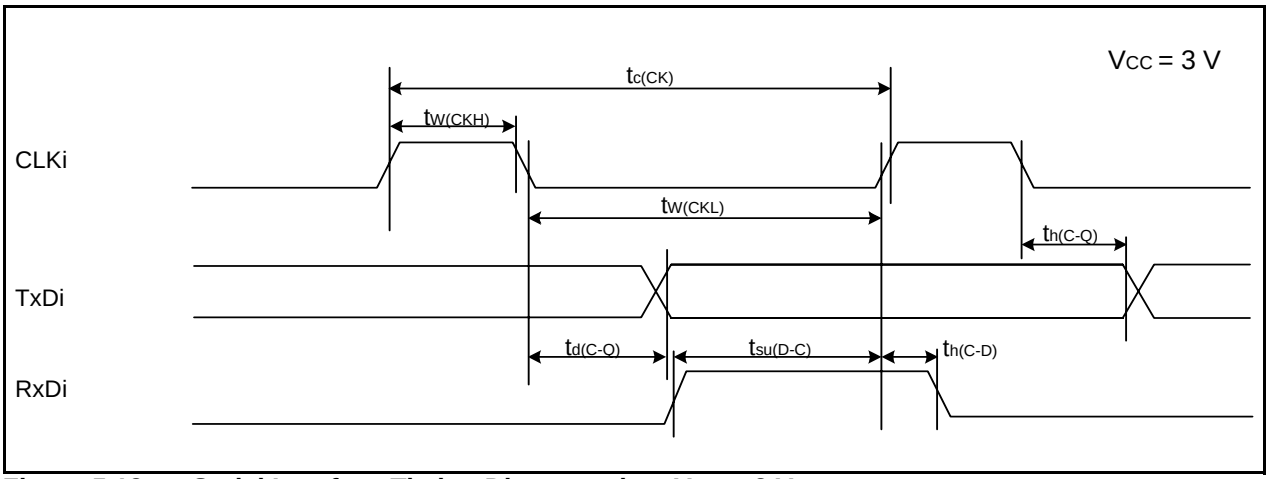


Figure 5.12 Serial Interface Timing Diagram when Vcc = 3 V

Table 5.25 External Interrupt $\overline{INT0}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INT0}$ input “H” width	380(1)	–	ns
$t_{W(INL)}$	$\overline{INT0}$ input “L” width	380(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{INT0}$ input filter select bit, use an $\overline{INT0}$ input HIGH width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INT0}$ input filter select bit, use an $\overline{INT0}$ input LOW width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater.

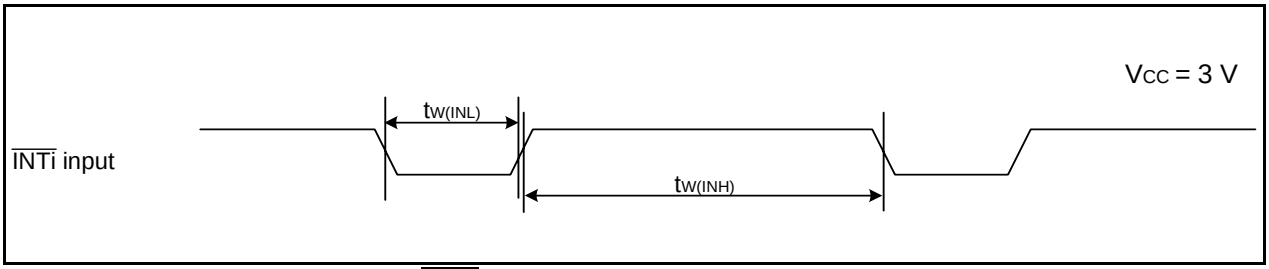


Figure 5.13 External Interrupt $\overline{INT0}$ Input Timing Diagram when Vcc = 3 V

REVISION HISTORY	R8C/18 Group, R8C/19 Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.10	Nov 15, 2004	–	First Edition issued
0.20	Jan 11, 2005	5, 6	Tables 1.3 and 1.4: The date updated
0.21	Apr 04, 2005	2, 3	Tables 1.1 and 1.2: Partly revised
		4	Figure 1.1: Partly revised
		5, 6	Tables 1.3 and 1.4: Partly revised
		5, 6	Figure 1.2 and 1.3: Partly revised
		7, 8	Figure 1.4 and 1.5: Partly revised
		10	Table 1.6: Partly revised
		16	Table 4.1: Partly revised
		17	Table 4.2: Partly revised
		18	Table 4.3: Partly revised
		20	Package Dimensions are revised
1.00	May 27, 2005	5, 6	Tables 1.3 and 1.4: Partly revised
		9	Table 1.5: Partly revised
		25	Table 5.9: Revised
		26	Table 5.10: Partly revised
		28	Table 5.13: Partly revised
		32	Table 5.20: Partly revised
1.10	Jun 09, 2005	26	Table 5.10: Partly revised
1.20	Nov 01, 2005	3	Table 1.2 Performance Outline of the R8C/19 Group; Flash Memory: (Data area) → (Data flash) (Program area) → (Program ROM) revised
		4	Figure 1.1 Block Diagram; “Peripheral Function” added, “System Clock Generation” → “System Clock Generator” revised
		6	Table 1.4 Product Information of R8C/19 Group; ROM capacity: “Program area” → “Program ROM”, “Data area” → “Data flash” revised
		9	Table 1.5 Pin Description; Power Supply Input: “VCC/AVCC” → “VCC”, “VSS/AVSS” → “VSS” revised Analog Power Supply Input: added
		11	Figure 2.1 CPU Register; “Reserved Area” → “Reserved Bit” revised
		13	2.8.10 Reserved Area; “Reserved Area” → “Reserved Bit” revised
		15	3.2 R8C/19 Group, Figure 3.2 Memory Map of R8C/19 Group; “Data area” → “Data flash”, “Program area” → “Program ROM” revised